

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLV31** is Designed for use in VHF amplifiers

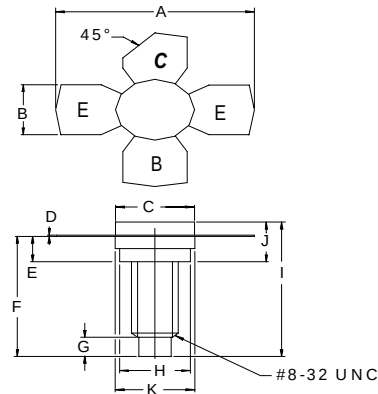
FEATURES:

- $P_G = 16.5$ dB Typical at 224 MHz
- **Omnigold™** Metallization System

MAXIMUM RATINGS

I_C	3A
V_{CB}	60 V
P_{DISS}	48 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	3.5°C/W

PACKAGE STYLE .280 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 100$ mA	30			V
BV_{CES}	$I_C = 25$ mA $V_{BE} = 0$ V	60			V
BV_{EBO}	$I_E = 10$ mA	4			V
h_{FE}	$V_{CE} = 25$ V $I_C = 800$ mA	15	75	120	---
C_{OB}	$V_{CB} = 25$ V $f = 1.0$ MHz		35		pF
P_{OUT} P_G	$V_{CE} = 25$ V $I_C = 800$ mA $P_{IN} = 2.5$ W $F = 224$ MHz $T = 70^\circ\text{C}$	5.0 15	7.0* 16.5*		W dB

* @ 25°C